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Nanotechnology & Microelectronics: Materials, Processing, Measurement, & Phenomena

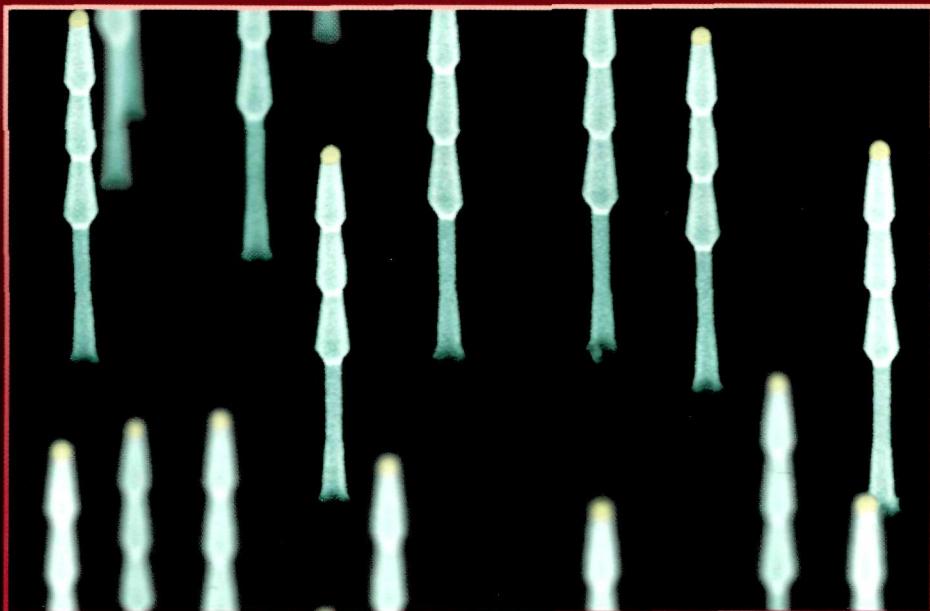


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Review Article:
Synthesis, Properties, and Applications of Silicon Nanocrystals
-by Lorenzo Mangolini

Papers from the 25th International Vacuum Nanoelectronics Conference



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Nanotechnology & Microelectronics:

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